

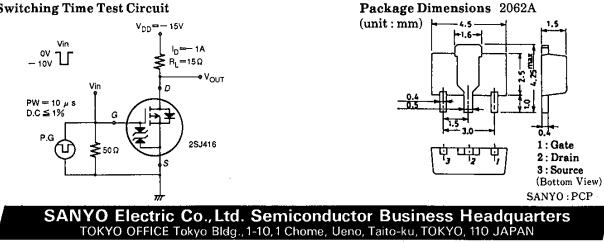
Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- \cdot 4V drive.

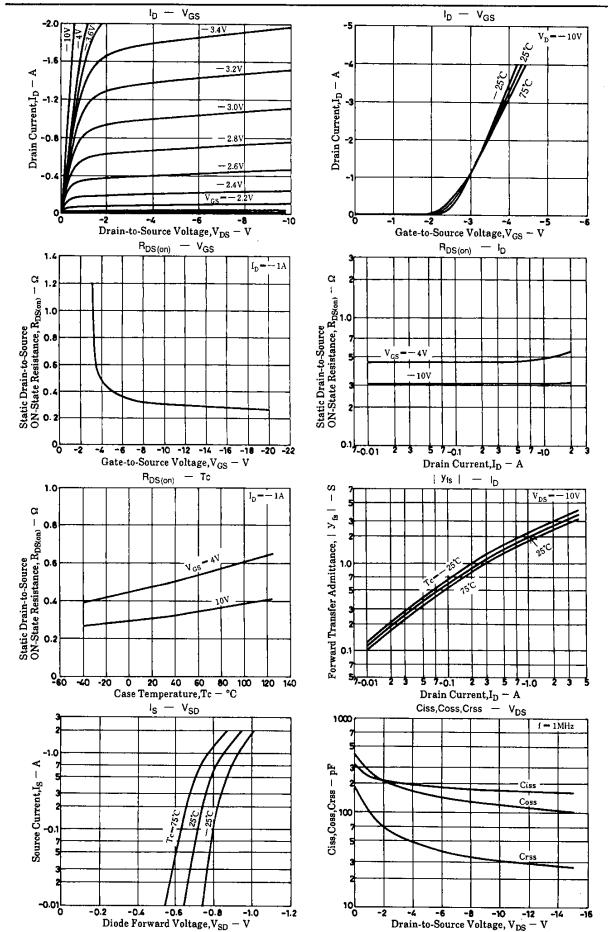
Absolute Maximum Ratings at Ta = 25°C				unit			
Drain-to-Source Voltage	V_{DSS}		-30 V		v		
Gate-to-Source Voltage	V_{GSS}		±20 V		v		
Drain Current(DC)	ID			-2	Α		
Drain Current(Pulse)	I _{DP}	PW≦10μs, duty cycle≦1%		-8	Α		
Allowable Power Dissipation	\mathbf{P}_{D}	Mounted on ceramic board		1.5	W		
·	-	$(250 \text{mm}^2 \times 0.8 \text{mm})$					
		$Tc = 25^{\circ}C$		3.5	W		
Channel Temperature	\mathbf{Tch}		150 °C		°C		
Storage Temperature	Tstg		-55 to +150 °C		°C		
·	-						
Electrical Characteristics at Ta =			min	typ	max	unit	
D-S Breakdown Voltage	V _{(BR)DSS}	$I_D = -1 m A, V_{GS} = 0$	-30			v	
{Zero-Gate Voltage	I _{DSS}	$V_{DS} = -30V, V_{GS} = 0$			-100	μΑ	
Drain Current							
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 16 V, V_{DS} = 0$			±10	μΑ	
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0		-2.5	v	
Forward Transfer Admittance		$V_{DS} = -10V, I_D = -1A$	1.2	2.0		S	
Static Drain-to-Source	R _{DS(on)}	$I_{D} = -1A, V_{GS} = -10V$		310	440	$m\Omega$	
ON-State Resistance	R _{DS(on)}	$I_{D} = -1A, V_{GS} = -4V$		480	650	$m\Omega$	
Input Capacitance	Ciss	$V_{DS} = -10V, f = 1MHz$		170		pF	
Output Capacitance	Coss	$V_{DS} = -10V, f = 1MHz$		120		pF	
Reverse Transfer Capacitance	Crss	$V_{DS} = -10V, f = 1MHz$		30		pF	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		10		ns	
Rise Time	tr	//		20		ns	
Turn-OFF Delay Time	$t_{d(off)}$	"	110		\mathbf{ns}		
Fall Time	tf	"		75		ns	
Diode Forward Voltage	V_{SD}	$I_{S} = -2A, V_{GS} = 0$		-1.0	-1.2	v	

Marking : JJ

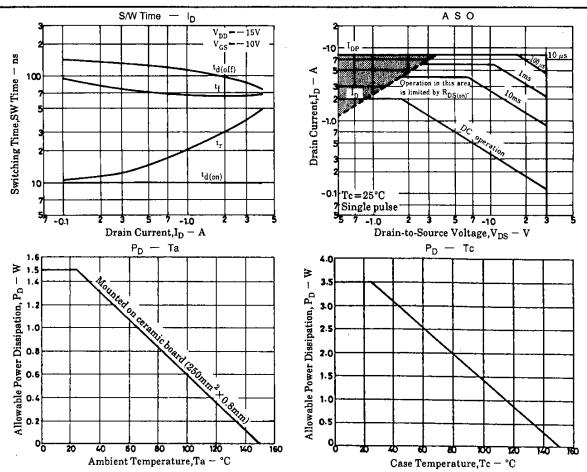
Switching Time Test Circuit

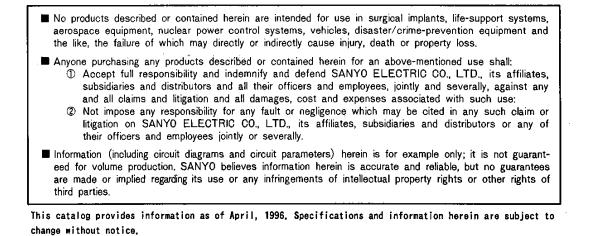


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No.5266-2/3





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